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2812

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
WSE	A1	5,637,531	6/10/97	Porowski et al.		
	A2	5,770,887	6/23/98	Tadatomo et al.		
	A3	5,810,925	9/22/98	Tadatomo et al.		
	A4					
	A5					
	A6					

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
WSE	B1	WO 95/04845	2/16/95	PCT		
WSE	B2	EP 0 937 790	8/25/99	European		

OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, etc.)

WSE	C1	Elsevier, Materials Science & Engineering B44, "Growth and Properties of Single Crystalline GaN Substrates and Homoepitaxial Layers", S. Porowski, pages 407-413, 1997.
/	C2	Elsevier, Diamond and Related Materials, "AMMONO Method of GaN and AlN Production", R. Dwilinski et al., Volume 7, pages 1348-1350, 1998.
/	C3	MRS Internet Journal of Nitride Semiconductor Research, "Near Defect Free GaN Substrates", S. Porowski, Volume 4S1, G1.3, 1999.
/	C4	Chem. Material, "Ammonothermal Synthesis of Cubic Gallium Nitride", Andrew P. Purdy, Volume 11, pages 1648-1651, 1999.
/	C5	Materials Research Society Symp. Proc., "Materials Chemistry and Bulk Crystal Growth of Group III Nitrides in Supercritical Ammonia", Joseph W. Kolis et al., Volume 495, pages 367-372, 1998.
/	C6	MRS Internet J. Nitride Semicond. Res. 4S1, G10.2, "GaN Homoepitaxy for Device Applications", M. Kamp et al., 1999.
	C7	Application RD-27,007 - "Crystalline Gallium Nitride and Method for Forming Crystalline Gallium Nitride".
✓	C8	Application RD-27,904 - "Homoepitaxial Gallium-Nitride-Based Light Emitting Device and Method for Producing".

EXAMINER

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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant